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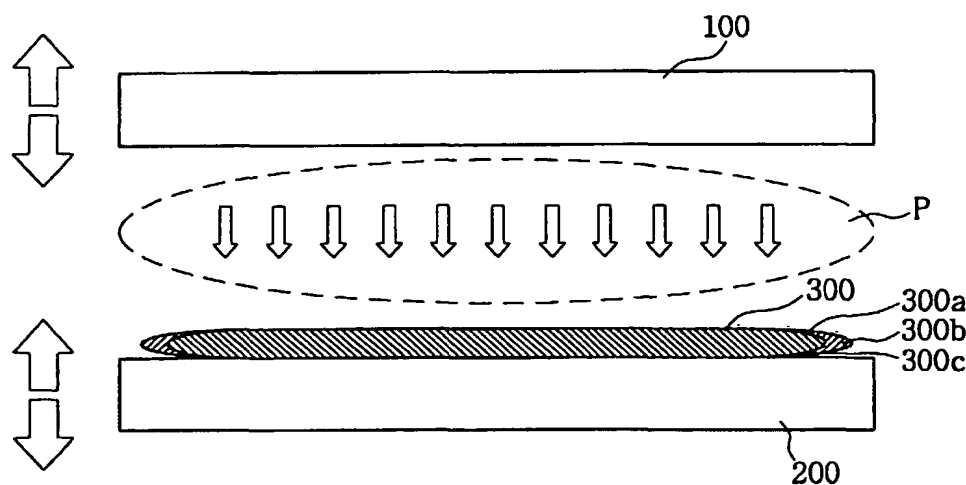
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(54) Title: METHOD FOR DRY ETCHING A SEMICONDUCTOR WAFER



(57) Abstract: Disclosed a method for dry etching a semiconductor wafer by a plasma generated between a power-supplied first electrode and a grounded second electrode. After the bottom surface of the edge of the wafer is in contact with the first electrode, and the top surface of the edge and the side surface of the wafer are etched by ionized plasma species generated by the plasma discharge of reactive ion etching. Then, after the upper surface of the edge of the wafer is in contact with the second electrode, and the bottom surface of the edge and the side surface of the wafer are etched by radicalized plasma species generated by the plasma discharge of plasma etching.



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